LE A P1W

OSRAM OSTAR® Projection Power

OSRAM OSTAR Projection Power is a high luminance LED for projection applications.



Applications

- Projection Home LED & Laser

- Projection Professional LED & Laser

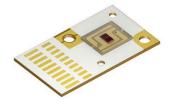
Features:

- Package: OSTAR High Power Projection
- Chip technology: Thinfilm
- Typ. Radiation: 120° (Lambertian emitter)
- Color: $\lambda_{dom} = 617 \text{ nm} (\bullet \text{ amber})$
- Corrosion Robustness Class: 3B
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

Ordering Information

| Туре | Luminous Flux ¹⁾ I _F = 12000 mA Φ_v | Ordering Code |
|------------------|--|---------------|
| LE A P1W-RSSP-23 | 1400 1940 lm | Q65112A7509 |





Maximum Ratings

| Parameter | Symbol | | Values |
|---|------------------|------|----------|
| Operating Temperature | T _{op} | min. | -40 °C |
| | - F | max. | 100 °C |
| Storage Temperature | T _{stg} | min. | -40 °C |
| | 0 | max. | 100 °C |
| Junction Temperature | T _j | max. | 125 °C |
| Forward Current | I _F | min. | 200 mA |
| $T_J = 125 \text{ °C}$; all chips operated in parallel | | max. | 10000 mA |
| Forward Current pulsed D = 0.6 ; f = 240 Hz; T_J = 25 °C; all chips operated in parallel | I_{Fpulse} | | 12000 mA |
| Surge Current $t_p \le 10 \ \mu$ s; D = 0.1; T _ = 125 °C; all chips operated in parallel | I _{FS} | max. | 16000 mA |
| ESD withstand voltage acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2) | V_{ESD} | | 2 kV |
| Reverse current ²⁾ | I _R | max. | 200 mA |



Characteristics

 T_{Board} = 25 °C; I_{F} = 12000 mA; f = 1000 Hz; t_{int} = 100 ms; D = 0.25; all chips operated in parallel

| Parameter | Symbol | | Values |
|--|------------------------------|----------------------|----------------------------|
| Peak Wavelength | λ_{peak} | typ. | 624 nm |
| Dominant Wavelength ³⁾ | λ_{dom} | min. typ. max. | 612 nm 617 nm 624 nm |
| Spectral bandwidth at 50% I _{rel,max} | Δλ | typ. | 18 nm |
| Viewing angle at 50% I_v | 2φ | typ. | 120 ° |
| Radiating surface | A _{color} | typ. | 1.5 x 2.6 mm ² |
| Partial Flux acc. CIE 127:2007 ⁴⁾ I _F = 12000 mA | $\Phi_{\rm E/V,\ 120^\circ}$ | typ. | 0.82 |
| Forward Voltage ⁵⁾ $I_F = 12000 \text{ mA}$; all chips operated in parallel | V _F | min. typ. max. | 2.80 V 3.00 V 4.00 V |
| Deviation of forward voltage of all chips | V _F | max. | 135 mV |
| Reverse voltage (ESD device) | V _{R ESD} | min. | 45 V |
| Reverse voltage ²⁾ I _R = 20 mA | V _R | max. | 1.2 V |
| Real thermal resistance junction/board 6) | $R_{thJBreal}$ | typ. max. | 0.9 1.1 |
| Electrical thermal resistance junction/board $^{\rm 6)}$ with efficiency $\eta_{\rm e}$ = 13 % | $R_{thJBelec.}$ | typ. max. | 0.78 0.96 |



Brightness Groups

| Group | Luminous Flux ¹⁾ I _F = 12000 mA | Luminous Flux ¹⁾ I _F = 12000 mA | |
|-------|--|--|--|
| | min. | max. | |
| | Φ_{V} | Φ_{V} | |
| RS | 1400 lm | 1500 lm | |
| RT | 1500 lm | 1640 lm | |
| RU | 1640 lm | 1800 lm | |
| SP | 1800 lm | 1940 lm | |

Wavelength Groups

| Group | Dominant Wavelength 3) | Dominant Wavelength ³⁾ |
|-------|------------------------|-----------------------------------|
| | min. | max. |
| | λ _{dom} | λ_{dom} |
| 2 | 612 nm | 618 nm |
| 3 | 618 nm | 624 nm |

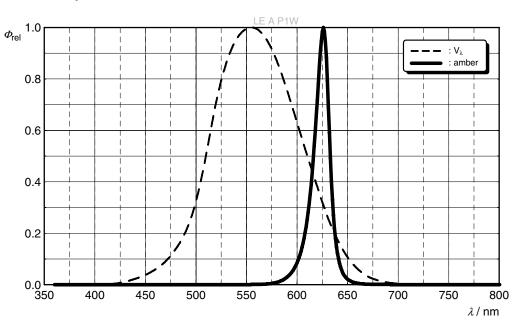
Group Name on Label

| Example: RS-2 Brightness | Wavelength |
|-----------------------------|------------|
| RS | 2 |



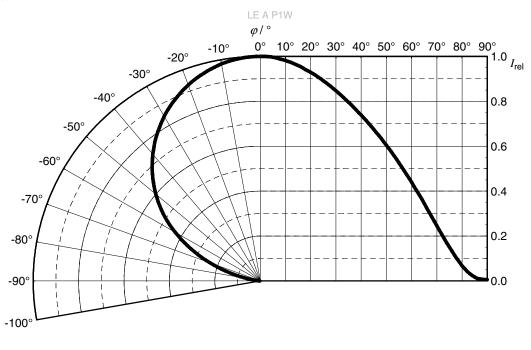
Relative Spectral Emission⁴⁾

 $\Phi_{_{rel}}$ = f (\lambda); I $_{_F}$ = 12000 mA; T $_{_J}$ = 25 °C; all chips operated in parallel



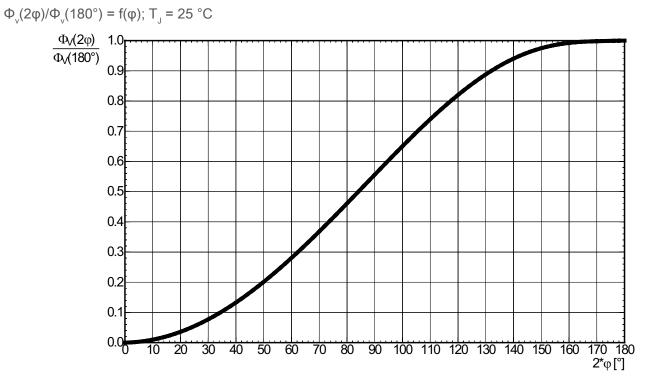
Radiation Characteristics⁴⁾

I_{rel} = f (φ); T_J = 25 °C





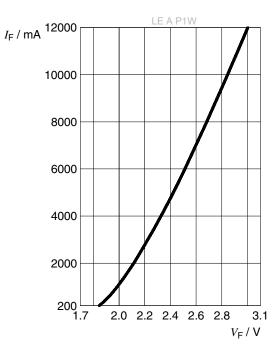
Relative Partial Flux⁴⁾





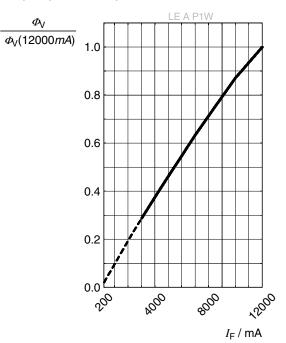
Forward current ^{4), 7)}

 $I_{_{F}} = f(V_{_{F}}); T_{_{J}} = 25 \text{ °C};$ all chips operated in parallel



Relative Luminous Flux ^{4), 7)}

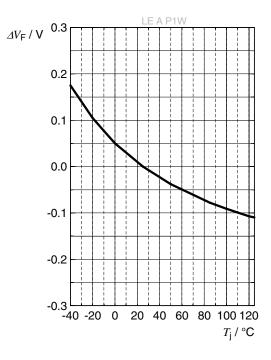
 $\Phi_v/\Phi_v(12000 \text{ mA}) = f(I_F); T_J = 25 \text{ °C};$ all chips operated in parallel





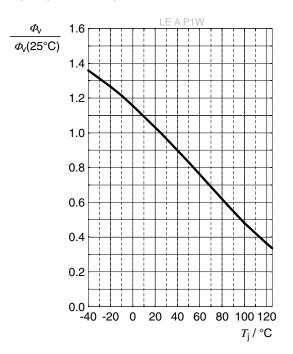
Forward Voltage ⁴⁾

 $\Delta V_F = V_F - V_F (25 \text{ °C}) = f(T_j); I_F = 12000 \text{ mA};$ all chips operated in parallel



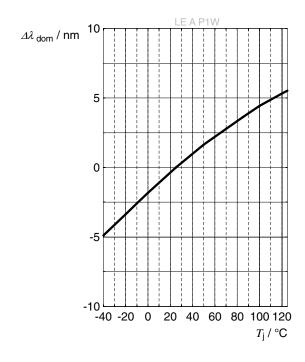
Relative Luminous Flux⁴⁾

 $\Phi_v/\Phi_v(25 \text{ °C}) = f(T_j); I_F = 12000 \text{ mA};$ all chips operated in parallel



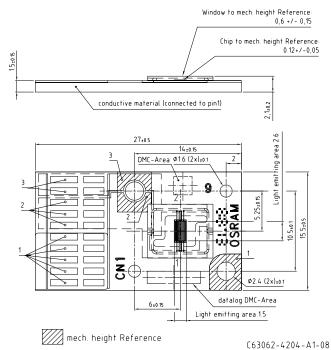
Dominant Wavelength⁴⁾

 $\Delta\lambda_{dom} = \lambda_{dom} - \lambda_{dom} (25 \text{ °C}) = f(T_j); \text{ I}_F = 12000 \text{ mA};$ all chips operated in parallel





Dimensional Drawing ⁸⁾

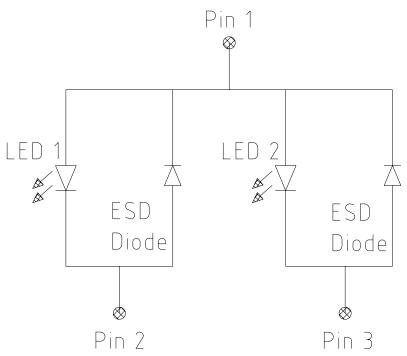


Further Information:

| Approximate Weight: | 5,000.0 mg |
|-------------------------------|---|
| Corrosion test: | Class: 3B Test condition: 40°C / 90 % RH / 15 ppm H ₂ S / 14 days (stricter than IEC 60068-2-43) |
| ESD advice: | The device is protected by ESD device which is connected in parallel to the Chip. |
| Notes: | Package not suitable for any kind of wet cleaning or ultrasonic cleaning. |
| Connector: | Recommended connector: Molex Pico-SPOX™ Wire-to-Board Header, Part Number 87438-1043 |
| Recommended mating connector: | Crimp Receptacle: Molex Pico-SPOX™ Wire-to-Board Housing, Part Num- ber 87439-1000 Crimp Terminals: Molex Pico-SPOX™ Crimp Terminal, Part Number 87421-0000 |



Electrical Internal Circuit

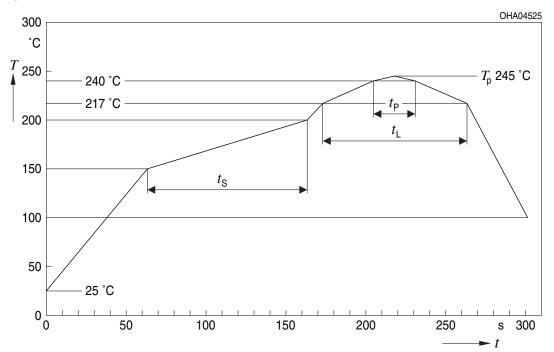


1: anode 2: cathode LED 1 3: cathode LED 2



Reflow Soldering Profile

Product complies to MSL Level 2 acc. to JEDEC J-STD-020E



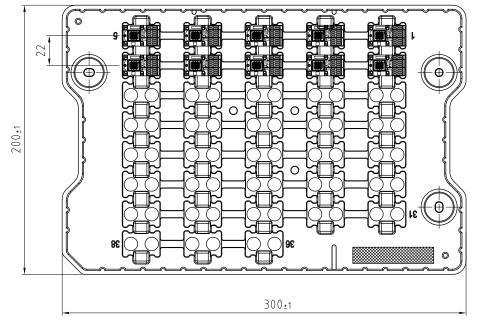
| Profile Feature | Symbol F | | Pb-Free (SnAgCu) Assembly | | Unit |
|--|----------------|---------|---------------------------|---------|------|
| | | Minimum | Recommendation | Maximum | |
| Ramp-up rate to preheat ^{*)} 25 °C to 150 °C | | | 2 | 3 | K/s |
| Time t _s T _{smin} to T _{Smax} | t _s | 60 | 100 | 120 | S |
| Ramp-up rate to peak ^{*)} T_{smax} to T_{p} | | | 2 | 3 | K/s |
| Liquidus temperature | TL | | 217 | | °C |
| Time above liquidus temperature | t | | 80 | 100 | S |
| Peak temperature | Τ _Ρ | | 245 | 260 | °C |
| Time within 5 °C of the specified peak temperature T_p - 5 K | t _P | 10 | 20 | 30 | S |
| Ramp-down rate* T _P to 100 °C | | | 3 | 6 | K/s |
| Time 25 °C to T _P | | | | 480 | S |

All temperatures refer to the center of the package, measured on the top of the component

* slope calculation DT/Dt: Dt max. 5 s; fulfillment for the whole T-range

LE A P1W

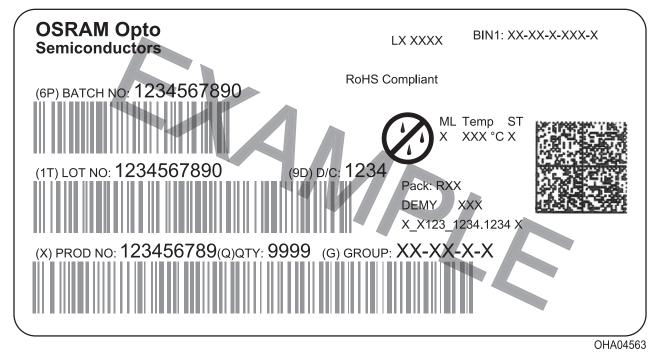
Taping⁸⁾



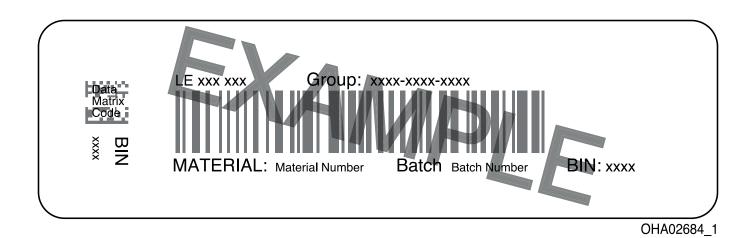
C63062-A4389-B10-01



Barcode-Product-Label (BPL)

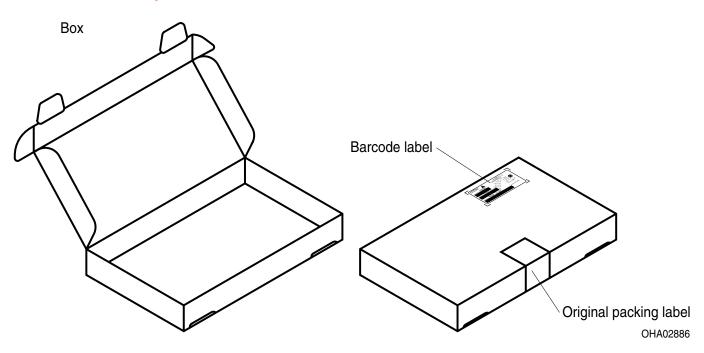


Barcode-Tray-Label (BTL)





Schematic Transportation Box ⁸⁾

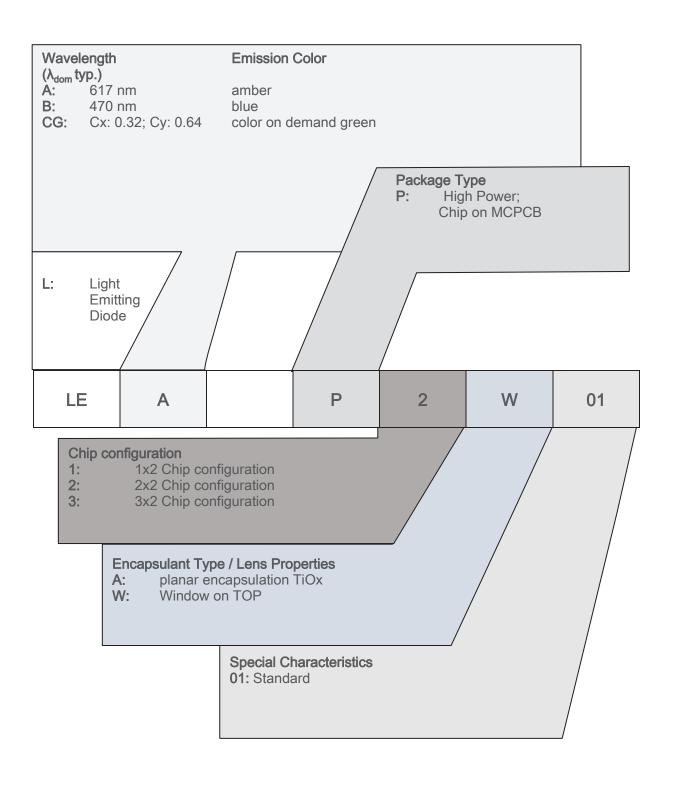


Dimensions of Transportation Box

| Width | Length | Height | |
|------------|-----------|-----------|--|
| 333 ± 5 mm | 218 ±5 mm | 28 ± 5 mm | |
| 337 ± 5 mm | 218 ±5 mm | 63 ± 5 mm | |



Type Designation System





Data Matrix Code Description

The Data Matrix Code bin information is Laser marked during testing Content: aaaa@bbbbb@cccc@ddddd@eeeee Data Matrix Code Type: ECC200

| a = Luminous Flux (Phiv) [Im] or Radiant Flux (Phie) [W] | (example: 3306) |
|--|------------------|
| b = Forward Voltage (Vf) [V] | (example: 3.46) |
| c = Wavelength (Ldom) [nm] | (example: 618) |
| d = Color Coordinate Cx | (example: 0.321) |
| e = Color Coordinate Cy | (example: 0.641) |
| @: Seperator = Blank | |



Notes

The evaluation of eye safety occurs according to the standard IEC 62471:2006 (photo biological safety of lamps and lamp systems). Within the risk grouping system of this IEC standard, the device specified in this data sheet falls into the class **exempt group (exposure time 10000 s)**. Under real circumstances (for exposure time, conditions of the eye pupils, observation distance), it is assumed that no endangerment to the eye exists from these devices. As a matter of principle, however, it should be mentioned that intense light sources have a high secondary exposure potential due to their blinding effect. When looking at bright light sources (e.g. headlights), temporary reduction in visual acuity and afterimages can occur, leading to irritation, annoyance, visual impairment, and even accidents, depending on the situation.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit www.osram-os.com/appnotes



Disclaimer

Attention please!

The information describes the type of component and shall not be considered as assured characteristics. Terms of delivery and rights to change design reserved. Due to technical requirements components may contain dangerous substances.

For information on the types in question please contact our Sales Organization.

If printed or downloaded, please find the latest version on the OSRAM OS website.

Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Product and functional safety devices/applications or medical devices/applications

OSRAM OS components are not developed, constructed or tested for the application as safety relevant component or for the application in medical devices.

OSRAM OS products are not qualified at module and system level for such application.

In case buyer – or customer supplied by buyer – considers using OSRAM OS components in product safety devices/applications or medical devices/applications, buyer and/or customer has to inform the local sales partner of OSRAM OS immediately and OSRAM OS and buyer and /or customer will analyze and coordinate the customer-specific request between OSRAM OS and buyer and/or customer.



Glossary

- ¹⁾ Brightness: Brightness values are measured during a pulse train of 100 ms with a pulse width of 250 µs and a frequencey of 1 kHz, with an internal reproducibility of +/- 8 % and an expanded uncertainty of +/- 11 % (acc. to GUM with a coverage factor of k = 3). The peak brightness is calculated according to the pulse duration and frequency.
- Reverse Operation: This product is intended to be operated applying a forward current within the specified range. Applying any continuous reverse bias or forward bias below the voltage range of light emission shall be avoided because it may cause migration which can change the electro-optical characteristics or damage the LED.
- ³⁾ **Wavelength:** The wavelength is measured during a pulse train of 100 ms with a pulse width of 250 μ s and a frequencey of 1 kHz, with an internal reproducibility of ± 0,5 nm and an expanded uncertainty of ± 1 nm (acc. to GUM with a coverage factor of k=3).
- ⁴⁾ Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- ⁵⁾ **Forward Voltage:** The forward voltage is measured during a pulse of typical 250 μs, with an internal reproducibility of +/- 0,05 V and an expanded uncertainty of +/- 0,1 V (acc. to GUM with a coverage factor of k=3).
- ⁶⁾ **Thermal Resistance:** Rth max is based on statistic values (6σ).
- ⁷⁾ **Characteristic curve:** In the range where the line of the graph is broken, you must expect higher differences between single devices within one packing unit.
- ⁸⁾ **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.



| Revision History | | |
|------------------|------------|---|
| Version | Date | Change |
| 1.12 | 2018-11-28 | Ordering Information Characteristics Electro - Optical Characteristics (Diagrams) New Layout |
| 1.13 | 2019-09-05 | Тгау |
| 1.14 | 2020-06-30 | Not for new design |
| 1.15 | 2020-10-13 | Discontinued |



LE A P1W

Discontinued

 Published by OSRAM Opto Semiconductors GmbH
 EU RoHS and China RoHS compliant product

 Leibnizstraße 4, D-93055 Regensburg
 www.osram-os.com © All Rights Reserved.

 此产品符合欧盟 RoHS 指令的要求;

按照中国的相关法规和标准,不含有毒有害物质或元素。



e